

## WET CLEANS FOR COBALT DISILICIDE PROCESSING

### Abstract of the Disclosure

*Sub>* A method for removing a formation of oxide of titanium that is generated as a byproduct of a process that forms cobalt disilicide within an insulated-gate field effect transistor (FET).

5     The method applies a chemical reagent to the FET at a predetermined temperature, and for a predetermined period of time, necessary for removing the formation, wherein the reagent does not chemically react with the cobalt disilicide. A reagent that accomplishes this task comprises water ( $H_2O$ ), ammonium hydroxide ( $NH_4OH$ ), and hydrogen peroxide ( $H_2O_2$ ), wherein the  $NH_4OH$  and the  $H_2O_2$  each comprise approximately 4% of the total reagent volume. An effective temperature is 65 °C combined with a 3 minute period of application.

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